

Vishay Siliconix

Automotive N-Channel 100 V (D-S) 175 °C MOSFET

PRODUCT SUMMARY				
V _{DS} (V)	100			
$R_{DS(on)}(\Omega)$ at $V_{GS} = 10 \text{ V}$	0.0036			
I _D (A) ^e	105			
Configuration	Single			

FEATURES

- TrenchFET® Gen IV power MOSFET
- AEC-Q101 qualified
- 100 % Rq and UIS tested
- Thin 1.9 mm height
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912



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N-Channel MOSFET S	

ORDERING INFORMATION	
Package	PowerPAK 8 x 8LR
Lead (Pb)-free and halogen-free	SQJQ118ER (for detailed order number please see www.vishay.com/doc?79776)

ABSOLUTE MAXIMUM RATINGS (T _C = 25 °C, unles		SYMBOL	LIMIT	UNIT
Drain-source voltage	V _{DS}	100	V	
Gate-source voltage	V _{GS}	± 20		
Continuous drain current ^e	T _C = 25 °C	1	105	
	T _C = 125 °C	- I _D	61	
Continuous source current (diode conduction) e		I _S	97	А
Pulsed drain current a, e		I _{DM}	423	
Single pulse avalanche current	L = 0.1 mH	I _{AS}	55	
Single pulse avalanche energy	L = 0.1 MH	E _{AS}	151	mJ
Maximum power dissipation c, e	T _C = 25 °C	Б	107	14/
	T _C = 125 °C	P_{D}	35	W
Operating junction and storage temperature range		T _J , T _{stg}	-55 to +175	°C
Soldering recommendations (peak temperature) c			260	1

THERMAL RESISTANCE RATINGS					
PARAMETER		SYMBOL	LIMIT	UNIT	
Junction-to-ambient	PCB mount b	R_{thJA}	40	°C/W	
Junction-to-case (drain) ^d		R _{thJC}	1.4	G/VV	

Notes

- a. Pulse test; pulse width $\leq 300~\mu s,$ duty cycle $\leq 2~\%$
- b. When mounted on 1" square PCB (FR4 material)
- c. See solder profile (www.vishay.com/doc?73257). The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection
- d. As per JESD51-14
- e. Values based on R_{thJC} and T_C of 25 °C. Actual values achievable will be dependent on the thermal characteristics of the complete system



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PARAMETER	SYMBOL	OL TEST CONDITIONS			TYP.	MAX.	UNIT	
Static								
Drain-source breakdown voltage	V _{DS}	$V_{GS} = 0$, $I_D = 250 \mu A$		100	-	-	V	
Gate-source threshold voltage	V _{GS(th)}	V _{DS} =	= V _{GS} , I _D = 250 μA	2	3	3.5	1	
Gate-source leakage	I _{GSS}	V _{DS} =	0 V, V _{GS} = ± 20 V	-	-	± 100	nA	
Zero gate voltage drain current		$V_{GS} = 0 V$	V _{DS} = 100 V	-	-	1		
	I _{DSS}	$V_{GS} = 0 V$	V _{DS} = 100 V, T _J = 125 °C	-	-	50	μΑ	
		$V_{GS} = 0 V$	V _{DS} = 100 V, T _J = 175 °C	1	-	500		
On-state drain current ^a	I _{D(on)}	$V_{GS} = 10 \text{ V}$	$V_{DS} \ge 5 V$	50	-	-	Α	
Drain-source on-state resistance ^a		$V_{GS} = 10 \text{ V}$	I _D = 20 A	ı	0.0028	0.0036		
	R _{DS(on)}	$V_{GS} = 10 \text{ V}$	I _D = 20 A, T _J = 125 °C	1	-	0.0074	Ω	
		$V_{GS} = 10 \text{ V}$	I _D = 20 A, T _J = 175 °C	1	-	0.0098		
Forward transconductance b	9 _{fs}	V _{DS} = 15 V, I _D = 25 A		ı	100	-	S	
Dynamic ^b								
Input capacitance	C _{iss}	V _{GS} = 0 V	V _{DS} = 25 V, f = 1 MHz	-	7213	10 099	pF	
Output capacitance	Coss			-	973	1445		
Reverse transfer capacitance	C _{rss}			-	54	84		
Total gate charge ^c	Q_g			ı	122	186		
Gate-source charge ^c	Q_{gs}	$V_{GS} = 10 \text{ V}$ $V_{DS} = 50 \text{ V}, I_D = 20 \text{ A}$	1	30	-	nC		
Gate-drain charge ^c	Q_{gd}			1	26		-	
Gate resistance	R_g	f = 1 MHz		0.4	1.1	2.2	Ω	
Turn-on delay time ^c	t _{d(on)}	$V_{DD} = 50 \text{ V}, \text{ R}_L = 2.5 \Omega,$ $I_D \cong 20 \text{ A}, \text{ V}_{GEN} = 10 \text{ V}, \text{ R}_g = 1 \Omega$		1	17	27	ns	
Rise time ^c	t _r			1	16	26		
Turn-off delay time ^c	t _{d(off)}			ı	48	74		
Fall time ^c	t _f			1	13	20		
Source-Drain Diode Ratings and Charact	teristics ^b							
Pulsed current ^a	I _{SM}			-	-	388	Α	
Forward voltage	V_{SD}	I _F = 40 A, V _{GS} = 0 V		-	0.7	1.1	V	
Body diode reverse recovery time	t _{rr}	I _F = 15 A, di/dt = 100 A/μs		-	63	126	ns	
Body diode reverse recovery charge	Q _{rr}			-	151	302	nC	
Reverse recovery fall time	t _a			ı	49	-		
Reverse recovery rise time	t _b			-	14	-	ns	
Body diode peak reverse recovery current	I _{RM(REC)}			_	-4.4	_	Α	

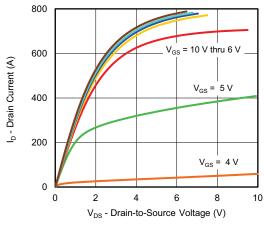
Notes

- a. Pulse test; pulse width $\leq 300~\mu s,~duty~cycle \leq 2~\%$
- b. Guaranteed by design, not subject to production testing
- c. Independent of operating temperature

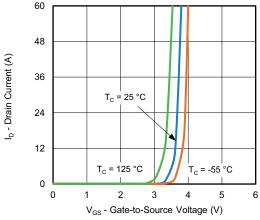
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



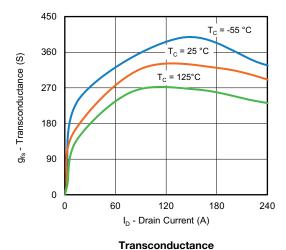
TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)

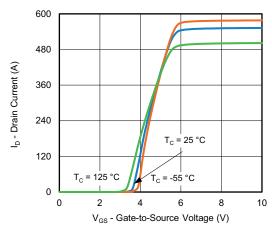


Output Characteristics

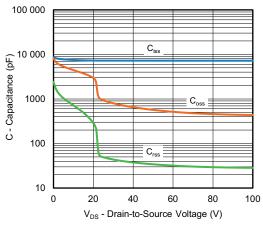


Transfer Characteristics

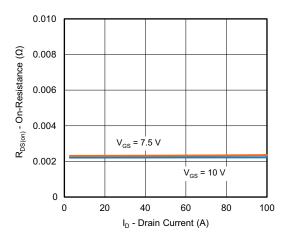




Transfer Characteristics



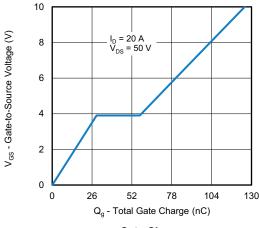
Capacitance



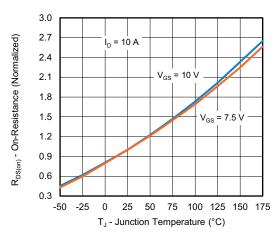
On-Resistance vs. Drain Current



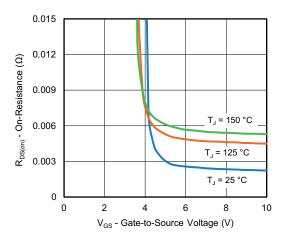
TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)



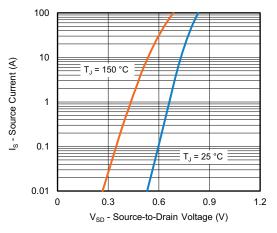




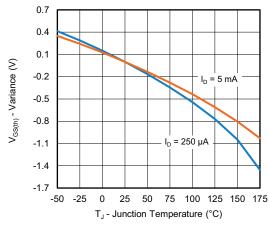
On-Resistance vs. Junction Temperature



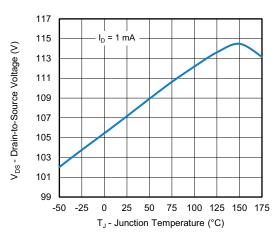
On-Resistance vs. Gate-to-Source Voltage



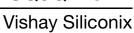
Source Drain Diode Forward Voltage



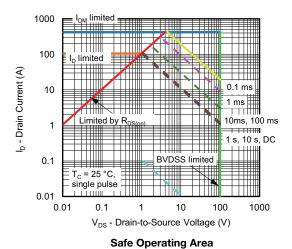
Threshold Voltage



Drain Source Breakdown vs. Junction Temperature





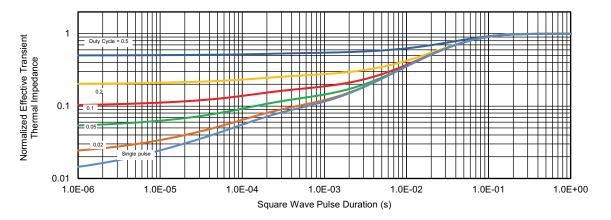


Note

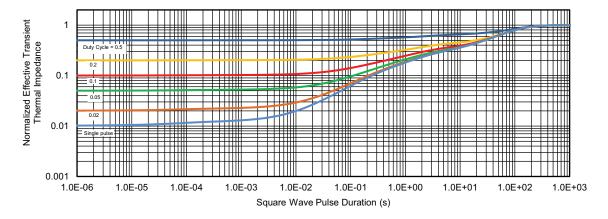
a. $V_{GS} > \mbox{minimum} \ V_{GS}$ at which $R_{DS(on)}$ is specified



THERMAL RATINGS (T_A = 25 °C, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Case



Normalized Thermal Transient Impedance, Junction-to-Ambient

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